Non-Inverting 3-State Buffer

The NL17SZ126 is a high performance single noninverting buffer operating from a 1.65 V to 5.5 V supply.

Features

- Extremely High Speed: t_{PD} 2.6 ns (typical) at V_{CC} = 5.0 V
- $\bullet\,$ Designed for 1.65 V to 5.5 V V_{CC} Operation
- Over Voltage Tolerant Inputs and Outputs
- LVTTL Compatible Interface Capability With 5.0 V TTL Logic with V_{CC} = 3.0 V
- LVCMOS Compatible
- 24 mA Balanced Output Sink and Source Capability
- Near Zero Static Supply Current Substantially Reduces System Power Requirements
- 3-State OE Input is Active HIGH
- Replacement for NC7SZ126
- Chip Complexity = 36 FETs
- Pb-Free Packages are Available

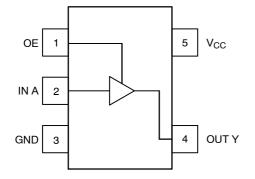


Figure 1. Pinout (Top View)

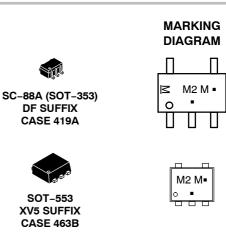


Figure 2. Logic Symbol



ON Semiconductor®

http://onsemi.com



M2 = Specific Device Code

- M = Date Code
- = Pb-Free Package

(Note: Microdot may be in either location) *Date Code orientation and/or position may vary depending upon manufacturing location.

PIN ASSIGNMENT					
1	OE				
2	IN A				
3	GND				
4	OUT Y				
5	V _{CC}				

FUNCTION TABLE

OE Input	A Input	Y Output
Н	L	L
Н	н	н
L	х	z

X = Don't Care

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V _{CC}	DC Supply Voltage		-0.5 to +7.0	V
V _{IN}	DC Input Voltage	-0.5 to +7.0	V	
V _{OUT}	DC Output Voltage	-0.5 to +7.0	V	
Ι _{ΙΚ}	DC Input Diode Current	-50	mA	
Ι _{ΟΚ}	DC Output Diode Current	- 50	mA	
I _{OUT}	DC Output Sink Current	± 50	mA	
I _{CC}	DC Supply Current per Supply Pin	±100	mA	
T _{STG}	Storage Temperature Range	-65 to +150	°C	
ΤL	Lead Temperature, 1 mm from Case for 10 Seconds		260	°C
TJ	Junction Temperature Under Bias		+ 150	°C
θ_{JA}	Thermal Resistance	SC-70/SC-88A	350	°C/W
PD	Power Dissipation in Still Air at 85°C	SC-70/SC-88A	150	mW
MSL	Moisture Sensitivity		Level 1	
F _R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	
V _{ESD}		Human Body Model (Note 2) Machine Model (Note 3) arged Device Model (Note 4)	>2000 >200 N/A	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability. 1. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2 ounce copper trace with no air flow.

2. Tested to EIA/JESD22-A114-A.

3. Tested to EIA/JESD22-A115-A.

4. Tested to JESD22-C101-A.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage	1.65	5.5	V
V _{IN}	DC Input Voltage	0	5.5	V
V _{OUT}	DC Output Voltage	0	5.5	V
T _A	Operating Temperature Range	- 40	+125	°C
t _r , t _f	Input Rise and Fall Time $V_{CC} = 1.8 \ V \pm 0.15 \ V \\ V_{CC} = 2.5 \ V \pm 0.2 \ V \\ V_{CC} = 3.0 \ V \pm 0.3 \ V \\ V_{CC} = 5.0 \ V \pm 0.5 \ V $	0 0	20 20 10 5.0	ns/V

DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

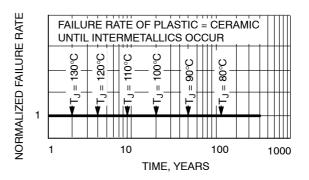


Figure 3. Failure Rate versus Time Junction Temperature

DC ELECTRICAL CHARACTERISTICS

		V _{CC}	$T_{A} = 25^{\circ}C \qquad -40^{\circ}C \leq T_{A} \leq 125^{\circ}C$		2	-40°C ≤ 1	A ≤ 125°C		
Symbol	Parameter	(V)	Min	Тур	Max	Min	Max	Unit	Condition
V _{IH}	High-Level Input Voltage	1.65 to 1.95 2.3 to 5.5	0.75 V _{CC} 0.7 V _{CC}			0.75 V _{CC} 0.7 V _{CC}		V	
V _{IL}	Low-Level Input Voltage	1.65 to 1.95 2.3 to 5.5			0.25 V _{CC} 0.3 V _{CC}		0.25 V _{CC} 0.3 V _{CC}	V	
V _{OH}	High–Level Output Voltage V _{IN} = V _{IH}	1.65 1.8 2.3 3.0 4.5	1.55 1.7 2.2 2.9 4.4	1.65 1.8 2.3 3.0 4.5		1.55 1.7 2.2 2.9 4.4		V	I _{OH} = −100 μA
		1.65 2.3 3.0 3.0 4.5	1.29 1.9 2.4 2.3 3.8	1.52 2.15 2.80 2.68 4.20		1.29 1.9 2.4 2.3 3.8		V	$\label{eq:1} \begin{array}{l} I_{OH} = -4 \text{ mA} \\ I_{OH} = -8 \text{ mA} \\ I_{OH} = -16 \text{ mA} \\ I_{OH} = -24 \text{ mA} \\ I_{OH} = -32 \text{ mA} \end{array}$
V _{OL}	Low-Level Output Voltage V _{IN} = V _{IL}	1.65 1.8 2.3 3.0 4.5		0.0 0.0 0.0 0.0 0.0	0.1 0.1 0.1 0.1 0.1		0.1 0.1 0.1 0.1 0.1	V	I _{OL} = 100 μA
		1.65 2.3 3.0 3.0 4.5		0.08 0.10 0.15 0.22 0.22	0.24 0.30 0.40 0.55 0.55		0.24 0.30 0.40 0.55 0.55	V	$I_{OL} = 4 \text{ mA}$ $I_{OL} = 8 \text{ mA}$ $I_{OL} = 16 \text{ mA}$ $I_{OL} = 24 \text{ mA}$ $I_{OL} = 32 \text{ mA}$
I _{IN}	Input Leakage Current	0 to 5.5			±1.0		±1.0	μA	$0~V \leq V_{IN} \leq 5.5~V$
I _{OZ}	3–State Output Leakage	1.65 to 5.5			±0.5		±5.0	μA	$\begin{array}{l} V_{IN} = V_{IH} \text{ or } V_{IL} \\ 0 \; V \leq V_{OUT} \leq 5.5 \; V \end{array}$
I _{OFF}	Power Off Leakage Current	0.0			1.0		10	μA	V_{IN} or V_{OUT} = 5.5 V
Icc	Quiescent Supply Current	1.65 to 5.5			1.0		10	μA	V _{IN} = 5.5 V, GND

AC ELECTRICAL CHARACTERISTICS ($t_R = t_F = 3.0 \text{ ns}$)

				v _{cc}	Т	A = 25°	С	$-40^{\circ}C \leq T$	A ≤ 125°C	
Symbol	Parameter	Condi	tion	(Ň)	Min	Тур	Max	Min	Мах	Unit
t _{PLH}	Propagation Delay	$R_L = 1 M\Omega$	C _L = 15 pF	1.8 ± 0.15	2.0	9.5	12	2.0	12.5	ns
t _{PHL}	AN to YN (Figures 4, and 5,	$R_L = 1 M\Omega$	C _L = 15 pF	2.5 ± 0.2	1.0	3.4	7.5	1.0	8.0	
	Table 1)	$\begin{array}{l} R_{L} = 1 \ M\Omega \\ R_{L} = 500 \ \Omega \end{array}$	C _L = 15 pF C _L = 50 pF	3.3 ± 0.3	0.8 1.2		5.2 5.7	0.8 1.2	5.5 6.0	
		$\begin{array}{l} R_{L} = 1 \ M\Omega \\ R_{L} = 500 \ \Omega \end{array}$	C _L = 15 pF C _L = 50 pF	5.0 ± 0.5	0.5 0.8		4.5 5.0	0.5 0.8	4.8 5.3	
t _{PZH}	Output Enable Time	R _L = 250 Ω	C _L = 50 pF	1.8 ± 0.15	2.0	9.0	10.5	2.0	12.5	ns
t _{PZL}	(Figures 6, 7 and 8, Table 1)			2.5 ± 0.2	1.8		8.5	1.8	9.0	
				3.3 ± 0.3	1.2		6.2	1.2	6.5	
				5.0 ± 0.5	0.8		5.5	0.8	5.8	
t _{PHZ}	Output Disable Time	R_L and $R1 = 500$	$\Omega \text{ C}_{\text{L}}$ = 50 pF	2.5 ± 0.2	1.5		8.0	1.5	8.5	ns
t _{PLZ}	(Figures 6, 7 and 8, Table 1)			2.5 ± 0.2	1.5		8.0	1.5	8.5	
				3.3 ± 0.3	0.8		5.7	0.8	6.0	
				5.0 ± 0.5	0.3		4.7	0.3	5.0	

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Unit
C _{IN}	Input Capacitance	V_{CC} = 5.5 V, V_I = 0 V or V_{CC}	2.5	pF
C _{OUT}	Output Capacitance	V_{CC} = 5.5 V, V_{I} = 0 V or V_{CC}	2.5	pF
C _{PD}	Power Dissipation Capacitance (Note 5)	10 MHz, V_{CC} = 3.3 V, V_{I} = 0 V or V_{CC} 10 MHz, V_{CC} = 5.5 V, V_{I} = 0 V or V_{CC}	9 11	pF

5. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no–load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.

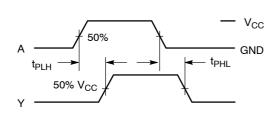
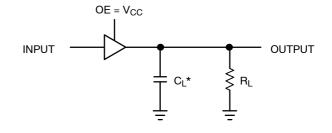
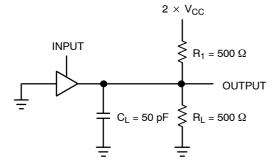


Figure 4. Switching Waveform



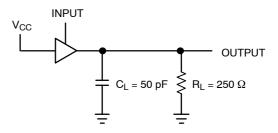
*Includes all probe and jig capacitance. A 1–MHz square input wave is recommended for propagation delay tests.





A 1–MHz square input wave is recommended for propagation delay tests.

Figure 6. t_{PZL} or t_{PLZ}



A 1–MHz square input wave is recommended for propagation delay tests.

Figure 7. t_{PZH} or t_{PHZ}

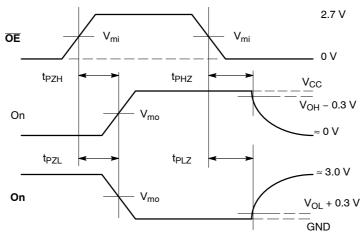




Table 1. Output Enable and Disable Times

 $t_{R} = t_{F} = 2.5$ ns, 10% to 90%; f = 1 MHz; $t_{W} = 500$ ns

	V _{cc}				
Symbol	$3.3 V \pm 0.3 V$	2.7 V	$2.5~V~\pm~0.2~V$		
V _{mi}	1.5 V	1.5 V	V _{CC/} 2		
V _{mo}	1.5 V	1.5 V	V _{CC/} 2		

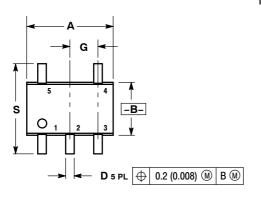
DEVICE ORDERING INFORMATION

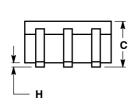
Device	Package Type	Shipping [†]
NL17SZ126DFT2	SC70-5/SC-88A/SOT-353	3000 / Tape & Reel
NL17SZ126DFT2G	SC70–5/SC–88A/SOT–353 (Pb–Free)	3000 / Tape & Reel
NL17SZ126XV5T2G	SOT–553 (Pb–Free)	4000 / Tape & Reel

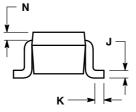
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

SC-88A, SOT-353, SC-70 CASE 419A-02 **ISSUE J**



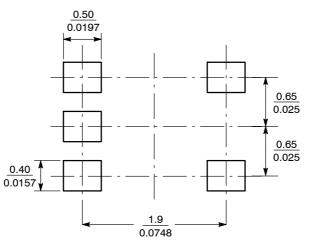




- NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH. 3. 419A-01 OBSOLETE. NEW STANDARD 419A-02. 4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	INC	HES	MILLIN	IETERS
DIM	MIN	MIN MAX		MAX
Α	0.071	0.087	1.80	2.20
В	0.045	0.053	1.15	1.35
С	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026	BSC	0.65 BSC	
Н		0.004		0.10
ſ	0.004	0.010	0.10	0.25
Κ	0.004	0.012	0.10	0.30
Ν	0.008 REF		0.20	REF
S	0.079	0.087	2.00	2.20

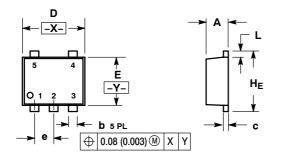
SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SOT-553, 5 LEAD CASE 463B ISSUE B



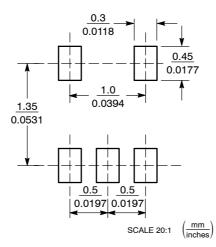
NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14 5M 1982

ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETERS

 MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.50	0.55	0.60	0.020	0.022	0.024
b	0.17	0.22	0.27	0.007	0.009	0.011
с	0.08	0.13	0.18	0.003	0.005	0.007
D	1.50	1.60	1.70	0.059	0.063	0.067
Е	1.10	1.20	1.30	0.043	0.047	0.051
е	0.50 BSC				0.020 BSC	;
L	0.10	0.20	0.30	0.004	0.008	0.012
HE	1.50	1.60	1.70	0.059	0.063	0.067

SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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